

The inelastic relaxation time due to electron-electron collisions in high-mobility two-dimensional systems under microwave radiations

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In some theoretical analyses of microwave-induced magnetoresistance oscillations in high-mobility two-dimensional systems, the "inelastic relaxation time" τ_{in} due to electron-electron scattering is evaluated using an equilibrium distribution function f^0 in the absence of radiation, and it is concluded that τ_{in} is much larger than τ_q , the single-particle relaxation time due to impurity scattering. However, under the irradiation of a microwave capable of producing magnetoresistance oscillation, the distribution function of the high-mobility electron gas deviates remarkably from f^0 at low temperatures. Estimating τ_{in} using an approximate nonequilibrium distribution function rather than using f^0 , one will find the system to be in the opposite limit $\tau_{in} = \tau_q$ even for $T = 0$ K. Therefore, models which depend on the assumption $\tau_{in} = \tau_q$ may not be justifiable.

The thermalization time τ_{th} , i.e. the time needed for system to approach the thermoequilibrium state, is an important property of an electron system in a nonequilibrium state. Though almost all the scattering mechanisms can contribute to τ_{th} , in many cases electron-electron scattering is the dominant one for thermalization, and the "inelastic relaxation time" τ_{in} due to electron-electron (ee) scattering in the nonequilibrium state can be approximately considered as τ_{th} . This τ_{in} has also served as an important parameter in several theoretical models of microwave-induced magnetoresistance oscillation in high-mobility two-dimensional systems. These models make use of the Boltzmann-type transport equation for the distribution function f with the ee collision term written in the form

$$\frac{\partial f}{\partial t} \Big|_{ee} = -\frac{f - f^0}{\tau_{in}}; \quad (1)$$

where f^0 is the equilibrium distribution function, i.e. the distribution function in the absence of radiation at lattice temperature T . Most of the existing treatments in the literature assume, explicitly or implicitly, that the distribution function f only slightly deviates from f^0 , such that τ_{in} can essentially be evaluated using the equilibrium distribution function f^0 and get at low temperature T

$$\frac{1}{\tau_{in}} = \frac{T^2}{2 E_F} \ln \frac{T}{E_F} \quad (2)$$

with E_F the Fermi energy of the two-dimensional (2D) electron system. For GaAs-based 2D electron system of carrier density $N_e = 3 \times 10^{15} \text{ m}^{-2}$, this yields

$$\tau_{in} = 10 \text{ mK} \text{ at } T = 1 \text{ K};$$

which is of the same order of magnitude as the disorder-limited inverse momentum (transport) relaxation time $\tau_m = 10 \text{ mK}$ if the system linear mobility is $\mu_0 = 2000 \text{ m}^2/\text{Vs}$, and may be much smaller than the inverse single-particle lifetime, τ_q , which can be as large as 0.5 K . The condition $\tau_{in} = \tau_q$ has been used as a key point in many theoretical treatments in the literature.

However, for ultra-clean (high-mobility) 2D electron systems under microwave irradiation of strength capable of producing photoresistance oscillation, the nonequilibrium distribution function f remarkably deviates from f^0 at low temperatures. The ee collision term in the transport equation generally can not be written in a form of Eq.(1). Even if, for an approximate analysis, one still takes Eq.(1) in the main equations, τ_{in} should be calculated using the nonequilibrium distribution function f rather than using f^0 . Though we may not know the exact nonequilibrium distribution function f under the influence of a strong electric field E_s , it is, in any case, much closer to the shifted function $f^0(k - mv_d)$ than to $f^0(k)$, the equilibrium distribution function in the absence of electric field. Here k stands for wavevector and v_d is the drift velocity under electric field E_s . With this nonequilibrium distribution function we have

$$\frac{1}{\tau_{in}} = \frac{1}{4 E_F} \ln \frac{E_F}{E_F} + \frac{1}{2} \dots; \quad (3)$$

even at $T = 0$ K. Here the excitation energy can be as large as

$$\epsilon_m = \frac{1}{2} m v_d^2 = 1 + 2 \frac{v_F}{v_d};$$

For the system of $\mu_0 = 2000 \text{ m}^2/\text{Vs}$ subject to an electric field of $E_s = 0.5 \text{ V/cm}$, $v_d = 10^5 \text{ m/s}$, $\epsilon_m = 80 \text{ K}$ and τ_{in} can be as high as 20 K , with an average around

$$\tau_{in} = 10 \text{ K};$$

Which is not only much larger than $\tau_m = 10 \text{ mK}$ but also much larger than $\tau_q = 0.5 \text{ K}$.

Therefore, models which depend heavily on the assumption $\tau_{in} = \tau_q$ may not be justifiable, even without considering other mechanisms for system thermalization.